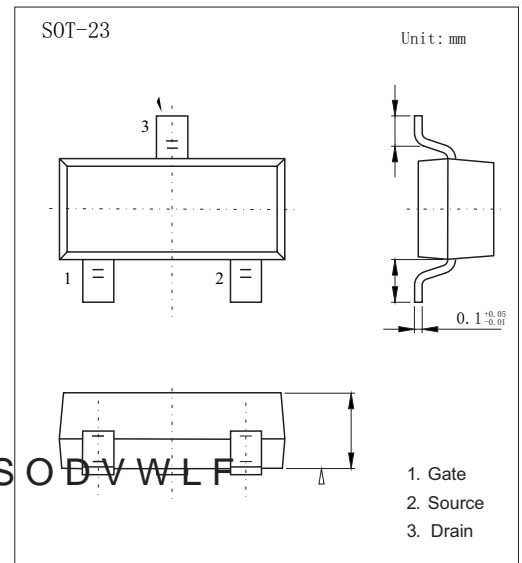


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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current	I _D	0.17	A
Pulsed Drain Current	I _{DM}	0.68	
Power Dissipation	P _D	0.36	W
Derate Above 25°C		2.8	□□□
Thermal Resistance, Junction-to-Ambient	R _{θJA}	350	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 5 5 t o 1 5 0	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250μA, V _{GS} =0V	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	
		V _{DS} =100V, V _{GS} =0V, T _J =55°C			60	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±10	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ; I _D =1mA	0.8			V
		V _{GS} =10V, I _D =0.17A			6	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =0.17A □ T _J =125°C			12	Ω
		V _{GS} =4.5V, I _D =0.17A			10	
On-State Drain Current	I _{D(on)}	V _{GS} =10V, V _{DS} =5V	0.68			A
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =0.17A	0.08			S
Input Capacitance	C _{iss}			73		
Output Capacitance	C _{oss}	V _{GS}		7		
Reverse Transfer Capacitance	C _{rss}			3.4		
Gate Resistance	R _g	V _{GS} =15mV, f _i =1MHz		2.2		Ω
Total Gate Charge	Q _g			1.8	2.5	
Gate-Source Charge	Q _{gs}			0.2		
Gate-Drain Charge	Q _{gd}			0.3		
Turn-On Delay Time	t _{d(on)}			1.7	3.4	
Turn-On Rise Time	t _r	V _{DD} ≠3.0V, I _D ≠0.28A, □		9		
Turn-Off Delay Time	t _{d(off)}	V _{GS} ≠1.0V, I _{RGEN} ≠6Ω		17	31	ns
Turn-Off Fall Time	t _f			2.4	5	
Body Diode Reverse Recovery Time	t _{rr}			11		
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =0.17A, I _d /dt=100A/μs		3		
Maximum Body Diode Continuous Current	I _S				0.17	A
Diode Forward Voltage	V _{SD}	I _S =0.34A, V _{GS} =0V			1.3	V

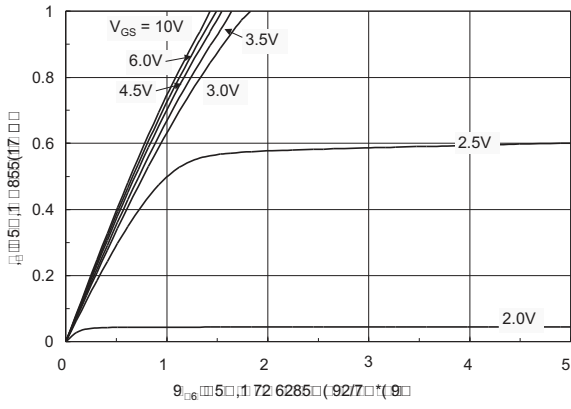


Figure 1: Drain current $I_{D,DC}$ vs. drain-source voltage V_{DS} for various gate-source voltages V_{GS} .

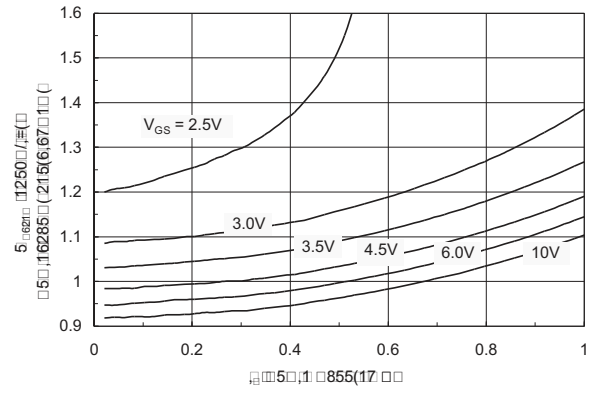


Figure 2: Drain current $I_{D,DC}$ vs. drain-source voltage V_{DS} for various gate-source voltages V_{GS} in a different region.

